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14. (Newly Added) A semiconductor device comprising:
- a pair of impurity regions, one of said pair forming a source and the other of said pair forming a drain in a semiconductor substrate; and
- a gate having a gate electrode disposed on said semiconductor substrate, said gate electrode having sidewalls disposed on either side thereof, wherein each of said pair of impurity regions further comprises a first impurity region and a thermally diffused second impurity region that is smaller than said first impurity region and said thermally diffused impurity region extends from a surface of said semiconductor substrate and below said gate electrode.
15. (Newly Added) A semiconductor device as recited in claim 14, wherein each of said thermally diffused impurity regions has an impurity concentration that is greatest at a vicinity of said surface and decreases with increasing depth from said surface.
16. (Newly Added) A semiconductor device as recited in claim 14, wherein said thermally diffused second impurity regions are formed from impurities from said sidewalls.
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17. A semiconductor device as recited in claim 14, wherein an impurity concentration of said first impurity regions is nearly the same as that of said second impurity regions.
18. A semiconductor device as recited in claim 14, wherein an impurity concentration of said second impurity regions is less than that of said first impurity regions.